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SOT-89 ṂṂ Ḫ PNP ÆṀ ч ‖ ㄱ Silicon PNP transistor in a SOT-89 Plastic Package.

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گ ₹ 3 Z ژ ı ч Ϟ ṇ ı љ 2SF2883 Ѝ ´

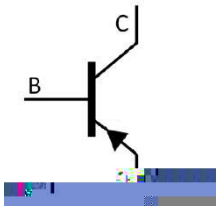
Suitable for output stage of 3 watts amplifier, small flat package, complementary to 2SC2883.

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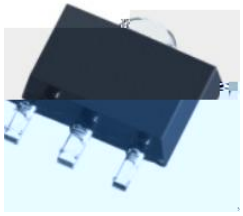
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Audio frequency amplifier applications.

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PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

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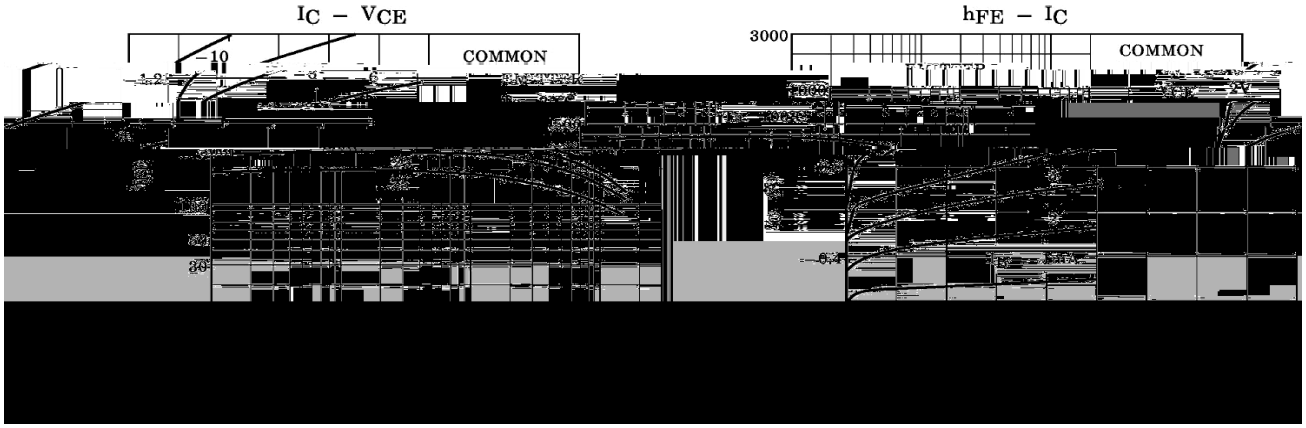
h_{FE} Classifications Symbol	O	Y
h_{FE} Range	100 200	160 320
Marking	HHO	HHY

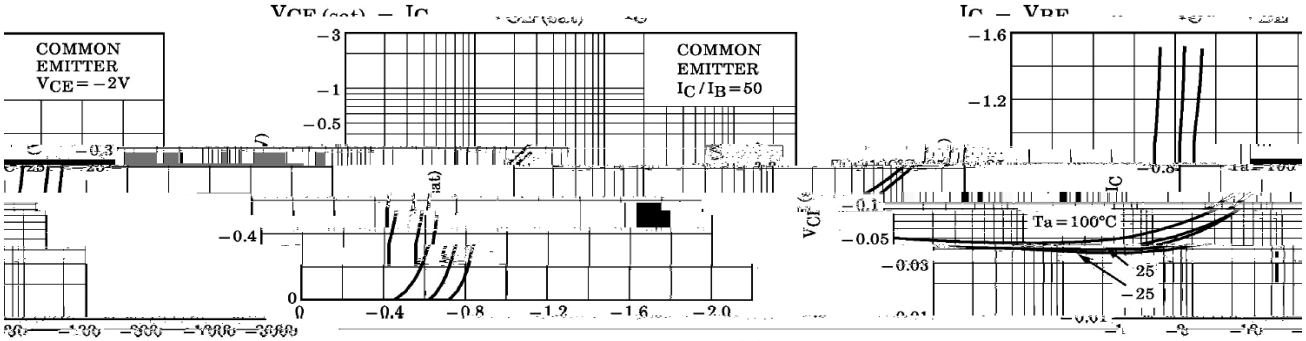
v ˝Ǫ Parameter	ϒ Symbol	˝Ǫ Ö Rating	D Ꮋ Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-1.5	A
Collector Base-Continuous	I_B	-0.3	A
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation*	*P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

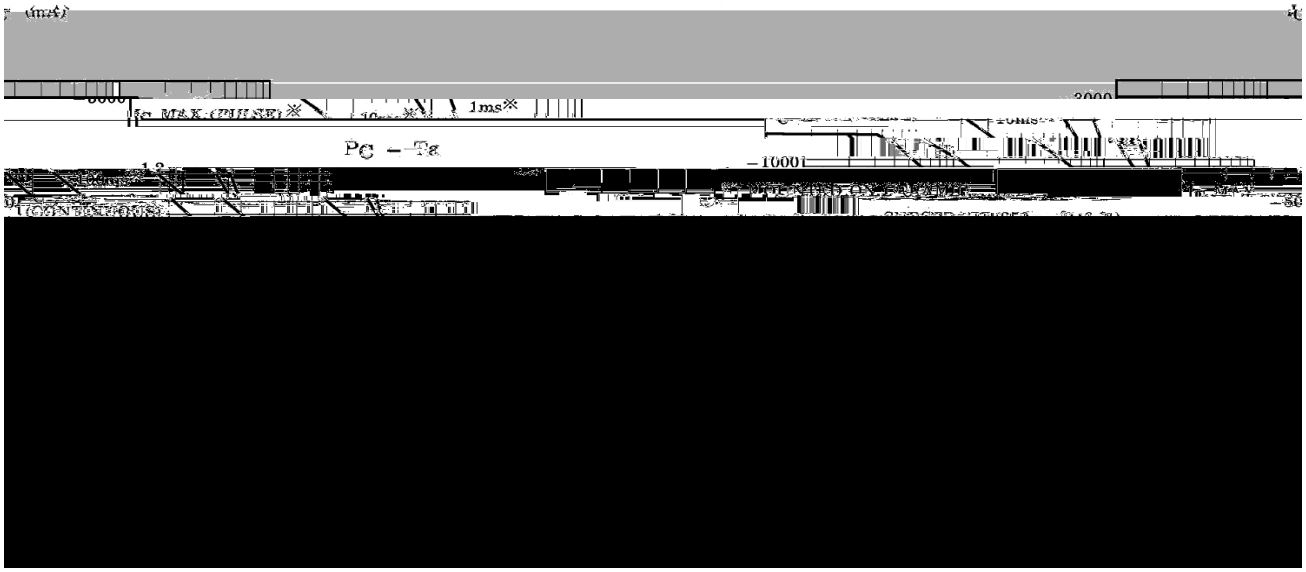
*mounted on ceramic substrate(250mm^2×0.8t)
-ˆ Ɛ^^ 283 p p ²Ö3.8W ÒBJ ь —

v ˝Ǫ Parameter	ϒ Symbol	Ш ː ǂ Ţ Test Conditions	ϣ ņ Ö Min	Ɛ ʒ Ö Typ	ϣ ᶻ Ö Max	D Ꮋ Unit
Collector to Emitter Breakdown Voltage	V_{CEO} I					

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IC – VCE
COMMON
hFE – IC
3000
COMMON

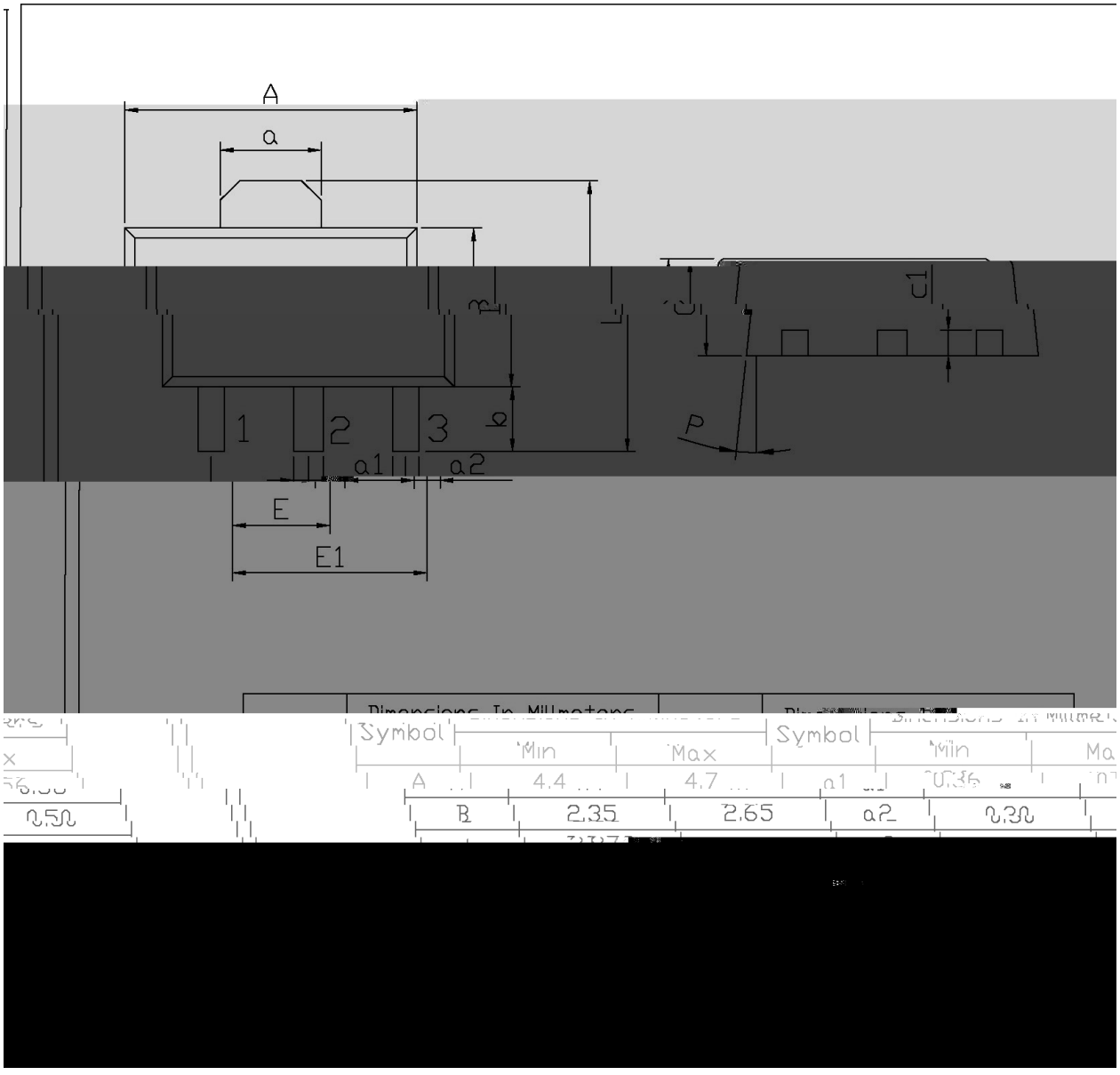

COMMON
EMITTER
VCE = −2V
COMMON
EMITTER
IC / IB = 50
−3
−1
−0.5
−0.4
0
−0.4
−0.8
−1.2
−1.6
−2.0
−1.6
−1.2
−0.1
−0.05
−0.03
Ta = 100°C
25
−25
VBE (V)


1ms※
PC – Ta
3000
1000

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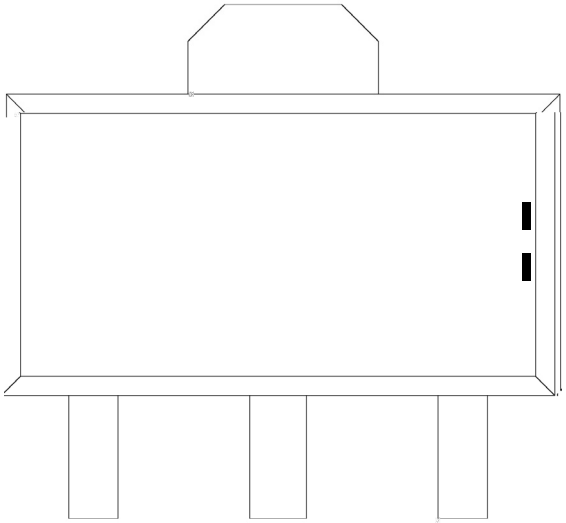
SOT-89

单位：mm



Symbol	Min	Max	Symbol	Min	Max
A	4.4	4.7	a1	0.35	
B	2.35	2.65	a2	0.30	

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ب ˝ χ

H χ ѭ ϛ Ղ

H χ ѭ ʒ Ղ

O χ ѭ h_{FE} ʿ ⁶ Ղ

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Note:

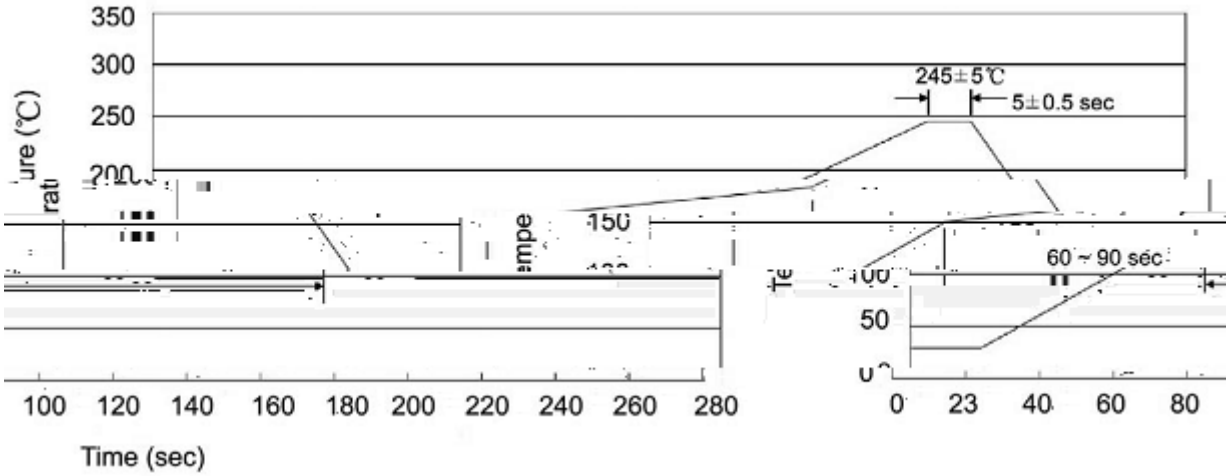
H: Company Code.

H: Product Type.

O: h_{FE} Classifications Symbol

**: Lot No. Code, code change with Lot No.

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ب ˝ χ

1 Ĺ ♬ □ ẙ 25 Ḱ 150 ɬ ı ˋH ڑ 60 Ḱ 90sec;

Note:

1.Preheating:25~150 ɬ